L Number	Hits	Search Text	DB	Time stamp
2	1395	`	USPAT;	2002/11/22 16:08
1		(257/360)).CCLS.	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
3	1293	((257/410) or (257/412)).CCLS.	USPAT;	2002/11/22 16:09
		(100)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1000	//057/620\ (257/625\ (257/620\	IBM_TDB	2002/11/22 16:00
4	1200	((257/632) or (257/635) or (257/638) or (257/639) or (257/649)).CCLS.	USPAT; US-PGPUB;	2002/11/22 16:09
		(237/033) 01 (237/043/).ccbb.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	3830	(((257/356) or (257/357) or (257/359) or	USPAT;	2002/11/22 16:10
		(257/360)).CCLS.) or (((257/410) or	US-PGPUB;	
		(257/412)).CCLS.) or (((257/632) or (257/635) or (257/638) or (257/639) or	EPO; JPO; DERWENT;	
		(257/649)).CCLS.)	IBM TDB	
6	52		USPAT;	2002/11/22 16:10
		(257/360)).CCLS.) or (((257/410) or	US-PGPUB;	
		(257/412)).CCLS.) or (((257/632) or	EPO; JPO;	
		(257/635) or (257/638) or (257/639) or	DERWENT;	
		(257/649)).CCLS.)) and silicon near3	IBM_TDB	
7	2	((((257/356) or (257/357) or (257/359) or	USPAT;	2002/11/22 16:12
	_	(257/360)).CCLS.) or (((257/410) or	US-PGPUB;	
		(257/412)).CCLS.) or (((257/632) or	EPO; JPO;	
		(257/635) or (257/638) or (257/639) or	DERWENT;	
		(257/649)).CCLS.)) and (silicon near3 oxygen near3 nitrogen near12 gate adj	IBM_TDB	
		insulat\$3)		
_	1399	((257/410) or (257/411) or	USPAT;	2001/10/04 11:30
		(257/412)).CCLS.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1078	((257/632) or (257/635) or (257/638) or	IBM_TDB USPAT;	2001/10/04 11:31
	1070	(257/639) or (257/649)).CCLS.	US-PGPUB;	2001/10/04 11:31
			EPO; JPO;	
			DERWENT;	
	2120	////8057/2568) /8257/2578)	IBM_TDB	2002/11/22 16:07
_	3139	(((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or	USPAT; US-PGPUB;	2002/11/22 16:07
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
		("257/635") or ("257/638") or ("257/639")	IBM_TDB	
		or ("257/649")).CCLS.)) and		
_	594	(@rlad<19990429 or @pd<19990428) ((((("257/356") or ("257/357") or	USPAT;	2001/10/04 11:44
	J74	(((((257/356) of (257/357) of ("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	2001/10/04 11.44
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
ļ		("257/635") or ("257/638") or ("257/639")	IBM_TDB	
**************************************		or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and		
		(gate near10 (insulation or insulator or		
		isolation or isolator))	1	
-	518	(((((("257/356") or ("257/357") or	USPAT;	2001/10/04 11:50
		("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or ("257/635") or ("257/638") or ("257/639")	DERWENT; IBM TDB	
		or ("257/649")).CCLS.)) and	TDM_TDB	
		(@rlad<19990429 or @pd<19990428)) and		
		(gate near10 (insulation or insulator or		
		isolation or isolator))) and (silicon or		
		polysilicon or polycrystalline near5		
	i	silicon)		

	·		T	1 0 0 0 1 (1 0 1 0 1 1 1 1 5 0
-	377	((((((("257/356") or ("257/357") or	USPAT; US-PGPUB;	2001/10/04 11:52
		("257/359") or ("257/360")).CCLS.) or ((("257/410") or ("257/411") or	EPO; JPO;	
		(((257/410)).CCLS.) or ((("257/632") or	DERWENT;	
		("257/635") or ("257/638") or ("257/639")	IBM TDB	
		or ("257/649")).CCLS.)) and	-5122	
		(@rlad<19990429 or @pd<19990428)) and		
		(gate near10 (insulation or insulator or		
		isolation or isolator))) and (silicon or		
		polysilicon or polycrystalline near5		
		silicon)) and (doped or dopant or doping)		
_	241	(((((((("257/356") or ("257/357") or	USPAT;	2001/10/04 11:55
		("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
		("257/635") or ("257/638") or ("257/639")	IBM_TDB	
		or ("257/649")).CCLS.)) and		
		(@rlad<19990429 or @pd<19990428)) and		
		(gate near10 (insulation or insulator or	1	
		isolation or isolator))) and (silicon or		
		polysilicon or polycrystalline near5		
		silicon)) and (doped or dopant or doping))		
		and (oxygen or oxynitride or silicon adj		
		dioxide)		0000 (10 (0) 10 ::
_	196	(((((((("257/356") or ("257/357") or	USPAT;	2001/10/04 13:44
		("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	
	1	((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
		("257/635") or ("257/638") or ("257/639")	IBM_TDB	
		or ("257/649")).CCLS.)) and		
		(@rlad<19990429 or @pd<19990428)) and (gate near10 (insulation or insulator or		
		isolation or isolator))) and (silicon or		
		polysilicon or polycrystalline near5		
		silicon)) and (doped or dopant or doping))		
		and (oxygen or oxynitride or silicon adj		
		dioxide)) and (nitrogen or oxynitride or		
		nitride)	-	
_	0	("L24 and silicon and oxygen and nitrogen	USPAT;	2001/10/04 13:47
		and first.clm. and second.clm.").PN.	US-PGPUB;	
		and lilberoim, and boomaroim, julii	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	7	((("6277708") or ("6236094") or	USPAT;	2001/10/04 13:50
	<u> </u>	("6191462") or ("6163050") or ("6133602")	US-PGPUB;	
		or ("6107657") or ("5962897") or	EPO; JPO;	
		("5923056") or ("5886368") or ("5838051")	DERWENT;	
		or ("5831319") or ("5828111") or	IBM TDB	
		("5811865") or ("5710454") or ("5635746")	-	
	-	or ("5619051") or ("5614748") or		
		("5596214") or ("5565691") or ("5412246")		
		or ("5289030") or ("5276346") or	1	
		("5268590") or ("5254867") or ("5237188")		
		or ("5134451") or ("4954867") or		
		("4931411") or ("4855247") or ("4814854")		
		or ("4698787") or ("3913211") or		
		("3863330") or ("3853633") or		
		("3724065")).PN.) and silicon and oxygen		
		and nitrogen and first.clm. and		
		second.clm.	L	

-	0	(((("6277708") or ("6236094") or	USPAT;	2001/10/04 13:50
		("6191462") or ("6163050") or ("6133602")	US-PGPUB;	
		or ("6107657") or ("5962897") or	EPO; JPO;	
	1	("5923056") or ("5886368") or ("5838051")	DERWENT;	
		or ("5831319") or ("5828111") or	IBM_TDB	
		("5811865") or ("5710454") or ("5635746")		
		or ("5619051") or ("5614748") or		
		("5596214") or ("5565691") or ("5412246")		
		or ("5289030") or ("5276346") or		1
		("5268590") or ("5254867") or ("5237188")		
		or ("5134451") or ("4954867") or		
		("4931411") or ("4855247") or ("4814854")		
		or ("4698787") or ("3913211") or		
		("3863330") or ("3853633") or		
		("3724065")).PN.) and silicon and oxygen		
		and nitrogen and first.clm. and		
		second.clm.) and sion		
-	1	(((("6277708") or ("6236094") or	USPAT;	2001/10/04 14:07
		("6191462") or ("6163050") or ("6133602")	US-PGPUB;	
İ		or ("6107657") or ("5962897") or	EPO; JPO;	
		("5923056") or ("5886368") or ("5838051")	DERWENT;	
		or ("5831319") or ("5828111") or	IBM TDB	
		("5811865") or ("5710454") or ("5635746")		
1		or ("5619051") or ("5614748") or		
		("5596214") or ("5565691") or ("5412246")		
		or ("5289030") or ("5276346") or		
		("5268590") or ("5254867") or ("5237188")		
		or ("5134451") or ("4954867") or		
		("4931411") or ("4855247") or ("4814854")		
		or ("4698787") or ("3913211") or		
	1	("3863330") or ("3853633") or		
		("3724065")).PN.) and silicon and oxygen		
		and nitrogen and first.clm. and		
		second.clm.) and silicon adj oxynitride		
_	0	((((("257/356") or ("257/357") or	USPAT;	2001/10/04 14:40
	Ĭ	("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	2002, 20, 01 21110
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
	1	("257/635") or ("257/638") or ("257/639")	IBM TDB	
		or ("257/649")).CCLS.)) and	12122	
		(@rlad<19990429 or @pd<19990428)) and		
		(silicon adj oxynitride with gate with		
		insulation) and (side adj wall adj spacer		
		with silicon with (oxide or dioxide))		
_	0	((((("257/356") or ("257/357") or	USPAT;	2001/10/04 14:40
		("257/359") or ("257/360")).CCLS.) or	US-PGPUB;	2001, 10, 01 11110
		((("257/410") or ("257/411") or	EPO; JPO;	
		("257/412")).CCLS.) or ((("257/632") or	DERWENT;	
		("257/635") or ("257/638") or ("257/639")	IBM TDB	
		or ("257/649")).CCLS.)) and		
		(@rlad<19990429 or @pd<19990428)) and		
		(silicon adj oxynitride with gate with		
		insulation) and side adj wall adj spacer		
_	0		USPAT;	2001/10/04 14:59
		insulation) and side adj wall adj spacer	US-PGPUB;	2001, 10, 01 11103
		insulation, and blue day wall day spacer	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	((silicon adj oxynitride or sion) with	USPAT;	2001/10/04 14:41
		gate with insulation) and side adj wall	US-PGPUB;	
		adj spacer	EPO; JPO;	
		aaj opacor	DERWENT;	
			IBM TDB	
_	0	((silicon adj oxynitride or sion) same	USPAT;	2001/10/04 14:42
		gate same insulation) and side adj wall	US-PGPUB;	=====================================
		adj spacer	EPO; JPO;	
		au spucer	DERWENT;	
			IBM TDB	,
1	1		1 1011 100	

	,		,	· · · · · · · · · · · · · · · · · · ·
-	2	((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or ((("257/410") or ("257/411") or ("257/412")).CCLS.) or ((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide) same gate same ((side adj wall) near10 (silicon adj oxide or silicon adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/04 14:46
-	5	dioxide)) ((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or ((("257/410") or ("257/411") or ("257/412")).CCLS.) or ((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/04 14:57
_	0	same gate same side adj wall ((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or ((("257/410") or ("257/411") or ("257/412")).CCLS.) or ((("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and (gate adj insulation adj film same "sio:n")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/04 14:57
-	0	(silicon adj oxinitride with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 14:59
_	0	(silicon adj (oxynitride or oxinitride) with gate with insulation) and side adj wall adj spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:00
_	137	((((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or ((("257/410") or ("257/411") or ("257/412")).CCLS.) or (("257/632") or ("257/635") or ("257/638") or ("257/639") or ("257/649")).CCLS.)) and (@rlad<19990429 or @pd<19990428)) and silicon same oxy\$7 same (oxide or dioxide) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/10/04 15:41
_	9	gate.ti,ab. and oxynitride.ti,ab. and (side adj wall with silicon with \$20xide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:53
	2022	side adj wall near10 (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:55
	80	side adj wall.ti. near10 (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:56
	89	side adj wall.ti. with (silicon adj oxide or silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/04 15:56

3 side addy wall.ti. with (silicon adj oxide) or silicon adj oxide) or silicon adj oxide) or polysilicon) adj gate 3 5620910.pn. USPAT; USP					
Delysilicon adj gate SPO; JPO; DENNENT; IBM TOB USPAT; USPORUB; IBM TOB US	-	3		ł .	2001/10/04 17:56
- 3 5620910.pn.					
1			polysilicon) adj gate	1	
3 5620910.pn. USPĀT; US-POFUB; EPG; JPG; DERWENT; IBM TDB USPĀT; US-POFUB; EPG; JPG; JPG; DERWENT; IBM TDB USPĀT; US-POFUB; DERWENT; IBM					
US-PECUES SPO. JPC) DERMENT: IBM TOB USPAT: U	_	٦ ء	5620910 pp		2001/10/04 16:32
Polysilicon adj gate.ti,ab. and (side adj using bare) Polysilicon adj using bare) Polysilico			3020310.pii.		2001/10/04 10:52
2 polysilicon adj gate.ti,ab. and (side adj USPAT; USP					
2 polysilicon adj gate.ti,ab. and (side adj USPAT; USP					
wall adj spacer near10 silicon adj US-PGFUB; EPO; JPO; DERNENT; IBM TOB USPAT; US-PGFUB; EPO; JPO; DERNENT; US-PGFUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J					
dioxide	_	2			2001/10/04 16:46
- 2 polysilicon adj gate.ti,ab. and (side adj wall adj spacer near5 silicon adj dioxide) - 3 5620910.pn.			1		
2			dioxide)		
2 polysilicon adj gate.ti,ab. and (side adj wall adj spacer near5 silicon adj dioxide) SPĀT; wall adj spacer near5 silicon adj dioxide) SPĀT; wall adj spacer near5 silicon adj dioxide) SPĀT; property Polyside					
Wali adj spacer near5 silicon adj dioxide US-PGPUB; EFO; JPO; DERWENT; IBM TOB USPAT; US-PGPUB; USPAT; US-	_	2	nolysilicon adi gate ti ab and (side adi	_	2001/10/04 16:55
Second S		_			2001/10/01 10:00
TIMM TDB USPAT; US-PGPUB; EEG; JPO; DERWENT; IEM TDB USPAT; US-PGPUB; EEO; JPO; DERWENT; IEM TDB USPAT; US			wall any spaces neare selection any alone as,		
- 12 (tungsten adj silicide near5 gate adj electrode) and gate adj insulation adj electrode) and gate adj insulation adj electrode near5 gate adj electrode near5 gate adj electrode near5 min mob uspan; and (257/\$5.ccls. or 438/\$5.ccls.) - 50 (field adj oxide near5 nitrogen) and (257/\$5.ccls. or 438/\$5.ccls.) - 110 gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon) gate adj electrode near5 doped adj silicon uspan; us-pecpub; ePo; JPO; DERMENT; IBM TOB uspan; us-pecpub; ePo; JPO; DERMENT; us-pecpub; ePo; JPO; derment ePo; ePo;					
12 (tungsten adj silicide near5 gate adj electrode) and gate adj insulation adj USPAT; USPGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPGPUB; EPO; JPO; DERWENT; USPGPUB; EPO;				IBM_TDB	
12 (tungsten adj silicide near5 gate adj DERWENT; LBM TOB USPĀT; USPGPDB, EPO; JPO; DERWENT; USPGPD	-	3	5620910.pn.		2001/10/04 17:01
12					
12					
12					
electrode) and gate adj insulation adj film - 3 5646054.pn. 5 5646054.pn. 5 50 (field adj oxide near5 nitrogen) and (257/\$5.cols. or 438/\$5.cols.) - 5 0 (field adj oxide near5 nitrogen) and (257/\$5.cols. or 438/\$5.cols.) - 10 gate adj electrode near5 doped adj silicon - 110 gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon) - 44 (gate adj electrode near5 doped adj silicon) - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.cols. - 22 (post-oxide or post adj oxide) adj film - 2001/10/04 21:21 2001/10/04 21:21	_	12	(tungsten adi silicide near5 gate adi		2001/10/04 17:03
Film		12			2001,10,01
- 3 5646054.pn. DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWEN					
- 35646054.pn. SPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US				1	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USP					
- 50 (field adj oxide near5 nitrogen) and (257/\$5.ccls. or 438/\$5.ccls.) - 110 gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon) - 44 (gate adj electrode near5 doped adj silicon) - 45 (gate adj electrode near5 doped adj silicon) - 46 (gate adj electrode near5 doped adj silicon) - 47 (gate adj electrode near5 doped adj silicon) - 48 (gate adj electrode near5 doped adj silicon) - 49 (gate adj electrode near5 doped adj silicon) - 40 (gate adj electrode near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 40 (gate adj electrode near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 41 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 42 (post-oxide or post adj oxide) adj film - 43 (gate adj electrode near5 doped adj silicon) - 44 (gate adj electrode near5 doped adj silicon) - 45 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 46 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 47 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 48 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 49 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 40 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 50 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 50 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls 50 (tunnel near6 gate near6	-	3	5646054.pn.		2001/10/04 17:56
- 50 (field adj oxide near5 nitrogen) and (257/\$5.ccls. or 438/\$5.ccls.) - 110 gate adj electrode near5 doped adj silicon - 110 gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon) - 44 (gate adj electrode near5 doped adj silicon) - 44 (gate adj electrode near5 doped adj silicon) - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride - 22 (post-oxide or post adj oxide) adj film - 3716 ((("257/356") or ("257/357") or ("257/357") or ("257/411") or ("257/432") or ("257/432") or ("257/632") or ("257/632") or ("257/633")					
- 50 (field adj oxide near5 nitrogen) and (257/\$5.ccls. or 438/\$5.ccls.) - 110 gate adj electrode near5 doped adj silicon - 44 (gate adj electrode near5 doped adj silicon berwent; IBM TDB USPĀT; US-PGPUB; EPG; JPG; DERWENT; IBM TDB US-PGPUB; EPG; JPG; DERWENT; IBM TDB US-PGPUB; EPG; JPG; DERWENT; IBM TDB US-PGPUB; EPG; JPG; DERWENT; IBM TD					
- 110 gate adj electrode near5 doped adj silicon gate adj electrode near5 doped adj silicon (gate adj electrode near5 doped adj silicon (gate adj electrode near5 doped adj silicon (gate adj electrode near5 doped adj silicon) (gate adj electrode ne					
110 gate adj electrode near5 doped adj silicon US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US	_	50	(field adi oxide near5 nitrogen) and		2001/10/04 20:20
- 110 gate adj electrode near5 doped adj silicon gate adj electrode near5 doped adj silicon (gate adj electrode near5 doped adj silicon uspām; uspām; uspēmbri, imm TDB uspām; uspām; uspēmbri, imm TDB uspām; uspām; uspēmbri, imm TDB uspām; uspām; uspēmbri, imm TDB uspām; uspām; uspām; uspām; uspām; uspām; uspēmbri, imm TDB uspām;		50			
- 110 gate adj electrode near5 doped adj silicon USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB;			, , , , , , , , , , , , , , , , , , , ,		
- 110 gate adj electrode near5 doped adj silicon USPĀT; US-PGPUB; EPC; JPC; DERWENT; IBM TDB USPĀT; US-PGPUB;				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JP					
- 44 (gate adj electrode near5 doped adj	_	110	gate adj electrode near5 doped adj silicon		2001/10/04 20:55
- 44 (gate adj electrode near5 doped adj silicon) and 257/\$5.ccls. - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 22 (post-oxide or post adj oxide) adj film - 22 (post-oxide or post adj oxide) adj film - 3716 ((("257/356") or ("257/357") or ("257/359") or ("257/411") or ("257/638") or ("257/638") or ("257/638") or ("257/639")					
- 44 (gate adj electrode near5 doped adj silicon) and 257/\$5.ccls. - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride - 22 (post-oxide or post adj oxide) adj film - 22 (post-oxide or post adj oxide) adj film - 3716 ((("257/356") or ("257/357") or ("257/357") or ("257/410") or ("257/411") or ("257/412") or ("257/412") or ("257/632") or ("257/632") or ("257/632") or ("257/635") or ("257/638") or ("257/639") 18M_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
- 44 (gate adj electrode near5 doped adj silicon) and 257/\$5.ccls. - 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride - 22 (post-oxide or post adj oxide) adj film - 22 (post-oxide or post adj oxide) adj film - 3716 ((("257/356") or ("257/357") or ("257/357") or ("257/411") or ("257/411") or ("257/411") or ("257/412") or ("257/638") or ("257/632") or ("257/635") or ("257/638") or ("257/639") - 3716 ("257/635") or ("257/638") or ("257/639")					
Silicon and 257/\$5.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; US-PGPUB; E	_	44	 (gate adi electrode near5 doped adi		2001/10/04 21:18
- 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 22 (post-oxide or post adj oxide) adj film USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 3716 ((("257/356") or ("257/357") or US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 3716 ((("257/359") or ("257/360")).CCLS.) or US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - WS-PGPUB; EPO; JPO; DERWENT; IBM_TDB - WS-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
- 133 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. - 1 (tunnel near6 gate near6 (insulation or insulating) adj film) and 257/\$5.ccls. and silicon adj oxynitride - 22 (post-oxide or post adj oxide) adj film - 3716 ((("257/356") or ("257/357") or ("257/359") or ("257/410") or ("257/410") or ("257/638") or ("257/638") or ("257/638") - 3716 (100000000000000000000000000000000000					
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- 22 (post-oxide or post adj oxide) adj film USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 3716 ((("257/356") or ("257/357") or ("257/359") or ("257/360")).CCLS.) or ("257/359") or ("257/410") or ("257/411") or ("257/412")).CCLS.) or (("257/632") or ("257/635") or ("257/638") or ("257/639") IBM_TDB IBM_TDB 2002/01/28 10:14 2002/01/28 11:26 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			silicon adj oxynitride	l	
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- 3716 ((("257/356") or ("257/357") or USPĀT; ("257/359") or ("257/360")).CCLS.) or US-PGPUB; ((("257/410") or ("257/411") or EPO; JPO; ("257/412")).CCLS.) or ((("257/632") or ERWENT; ("257/635") or ("257/638") or ("257/639") IBM_TDB					
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		("6107657") or ("5962897") or ("5923056")	EPO; JPO;	
		or ("5886368") or ("5838051") or	DERWENT;	
		("5831319") or ("5828111") or ("5811865")	IBM_TDB	
		or ("5710454") or ("5635746") or		
		("5619051") or ("5614748") or ("5596214")		
		or ("5565691") or ("5412246") or		
		("5289030") or ("5276346") or ("5268590")		
		or ("5254867") or ("5237188") or		
		("5134451") or ("4954867") or ("4931411")		1
		or ("4855247") or ("4814854") or		
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-	12	post-oxide adj film	USPAT;	2002/01/28 11:28
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-	6	post-oxide adj film and gate adj	USPAT;	2002/01/28 11:28
		insulating adj film	US-PGPUB;	
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	1		IBM_TDB	